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In the Claims:

1. (Currently amended) A semiconductor light emitting device of a II-VI group compound semiconductor formed on a compound semiconductor substrate and comprising an active layer between an n-type cladding layer and a p-type cladding layer, further comprising ~~an i-type semiconductor~~ a first barrier layer consisting of a single monolayer of an i-type ~~semiconductor material~~ $Zn_{1-x-y}Mg_xBe_ySe$ ($0 < x + y < 1$, $0 < x$, $0 < y$) having a band gap larger than a band gap of said p-type cladding layer, provided between and respectively directly in contact with said active layer and said p-type cladding [[~~layer.~~]] layer, wherein said active layer has a stacked structure including a quantum well layer and a second barrier layer, and wherein said n-type cladding layer is formed of $Zn_{1-x}Mg_xS_ySe_{1-y}$ ($0 < x < 1$, $0 < y < 1$).

2. (Withdrawn - Currently amended) The semiconductor light emitting device according to claim 1, wherein

said light emitting device of the II-VI group compound is a ZnSe based light emitting device; and

~~said n-type cladding layer is an n-type $Zn_{1-x}Mg_xS_ySe_{1-y}$ ($0 < x < 1$, $0 < y < 1$) layer; and~~

said p-type cladding layer is a p-type $Zn_{1-x}Mg_xS_ySe_{1-y}$ ($0 < x < 1$, $0 < y < 1$) layer.

3. (Currently amended) The semiconductor light emitting device according to claim 1, wherein a magnitude of the band gap of said first barrier layer is larger by 0.025 eV to 0.5 eV than the band gap of said p-type cladding layer.

4. (Currently amended) The semiconductor light emitting device according to claim 1, wherein in the band gap of said first barrier layer, an energy of a valence band is approximately the same as or higher than that of said p-type cladding layer, and an energy of a conductive band is larger than that of said p-type cladding layer.

Claims **5 to 11** (Canceled).

12. (Currently amended) The semiconductor light emitting device according to claim 1, wherein a thickness of said first barrier layer is at least 5 nm and at most equal to a thickness of said active layer.

13. (Original) The semiconductor light emitting device according to claim 1, wherein an n-type ZnSe single crystal substrate is used as said compound semiconductor substrate.

14. (Withdrawn) The semiconductor light emitting device according to claim 1, wherein an n-type GaAs single crystal substrate is used as said compound semiconductor substrate.

15. (Withdrawn - Currently amended) The semiconductor light emitting device according to claim 1, wherein in a stacked structure including said compound semiconductor substrate constituting said light emitting device which is a ZnSe based light emitting device, a deviation between a peak of X-ray diffraction of a plane orientation used as an index of distortion from said substrate and a peak of X-ray diffraction of said plane orientation from said stacked structure is at most 1000 seconds.

Claims **16 to 27** (Canceled).

28. (New) The semiconductor light emitting device according to claim 1, wherein said p-type cladding layer is formed of ZnCdS.

29. (New) The semiconductor light emitting device according to claim 1, wherein said p-type cladding layer is formed of ZnMgSSe.

[RESPONSE CONTINUES ON NEXT PAGE]